

Vishay Siliconix

Dual P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)						
- 30	0.087 at V _{GS} = - 10 V	- 4.5 ^a	3.2 nC						
	0.145 at V _{GS} = - 4.5 V	- 4.5 ^a	3.2 110						

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- APPLICATIONS

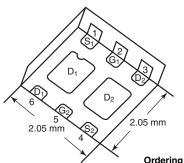
Power Switch for Motor Drive for Portable Devices

Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN

PowerPAK SC-70-6 Dual



 G_1 G_2 G_2

P-Channel MOSFET P-Channel MOSFET

Ordering Information:	SiA915DJ-T1-GE3	(Lead (Pb)-free a	and Halogen-free)
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ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
Parameter		Symbol	Limit	Unit				
Drain-Source Voltage		V _{DS}	- 30	V				
Gate-Source Voltage		V _{GS}	± 20					
	T _C = 25 °C		- 4.5 ^a					
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	I _D	- 4.5 ^a					
	T _A = 25 °C	טי [- 3.7 ^{b, c}					
	T _A = 70 °C		- 2.9 ^{b, c}	Α				
Pulsed Drain Current		I _{DM}	- 15					
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 4.5 ^a					
Continuous Source-Drain Diode Current	T _A = 25 °C	'8	- 1.6 ^{b, c}					
	T _C = 25 °C		6.5					
Maximum Power Dissipation	T _C = 70 °C	P _D	5	w				
Maximum Fower Dissipation	T _A = 25 °C	l 'b [1.9 ^{b, c}	VV				
	T _A = 70 °C		1.2 ^{b, c}					
Operating Junction and Storage Temperature Rar	T _J , T _{stg}	- 55 to 150	°C					
Soldering Recommendations (Peak Temperature)	d, e		260					

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W			
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	12.5	16	O/ VV			

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5.9
- d. See solder profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 110 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	•					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$			- 22		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		4.2		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 2.2	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zara Cata Valtaga Drain Current	,	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 10			Α
Drain Course On State Projectones	Б	V _{GS} = - 10 V, I _D = - 2.9 A		0.071	0.087	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 2.2 A		0.118	0.145	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 2.9 A		5		S
Dynamic ^b						
Input Capacitance	C _{iss}			275		
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		60		pF
Reverse Transfer Capacitance	C _{rss}			45		
Total Gate Charge	0	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.7 \text{ A}$		6	9	nC
	Qg			3.2	5	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.7 \text{ A}$		1.1		
Gate-Drain Charge	Q_{gd}			1.5		
Gate Resistance	R_{g}	f = 1 MHz	1.5	7.5	15	Ω
Turn-On Delay Time	t _{d(on)}			35	70	
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 5 \Omega$		25	50	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		15	30	
Fall Time	t _f			10	20	
Turn-On Delay Time	t _{d(on)}			7	15	ns
Rise Time	t _r	V_{DD} = - 15 V, R_L = 5 Ω		10	20	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		15	30	
Fall Time	t _f			10	20	1
Drain-Source Body Diode Characterist	ics					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.5	А
Pulse Diode Forward Current	I _{SM}				- 15	^
Body Diode Voltage	V_{SD}	I _S = - 3 A, V _{GS} = 0 V		- 0.87	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}	L = 2 A dl/dt = 100 A/vs T = 05 °C		7	14	nC
Reverse Recovery Fall Time	t _a	$I_F = -3 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		9.5		ns
Reverse Recovery Rise Time	t _b			5.5		

Notes:

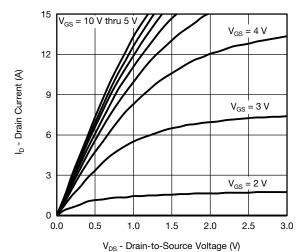
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

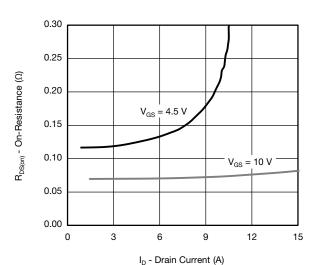


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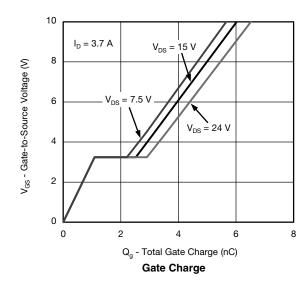
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

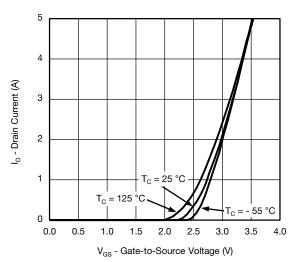


Output Characteristics

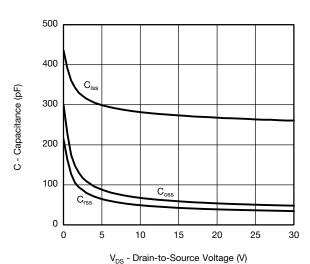


On-Resistance vs. Drain Current and Gate Voltage

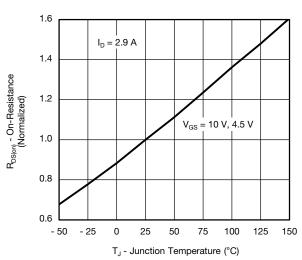




Transfer Characteristics



Capacitance



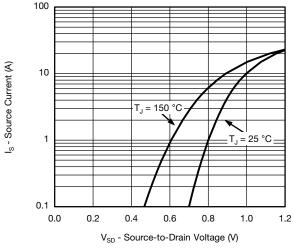
On-Resistance vs. Junction Temperature

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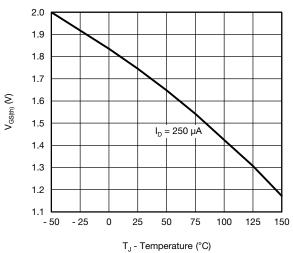
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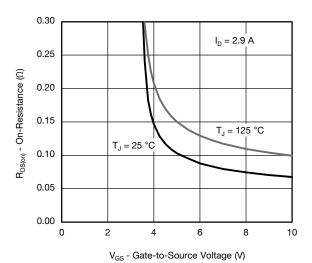
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



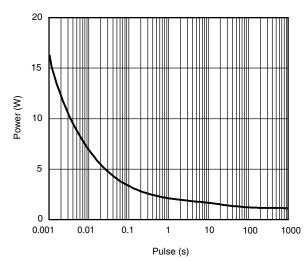
Source-Drain Diode Forward Voltage



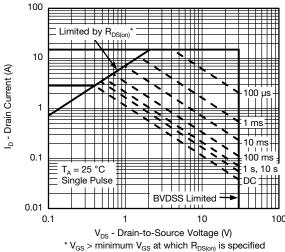
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified Safe Operating Area, Junction-to-Ambient

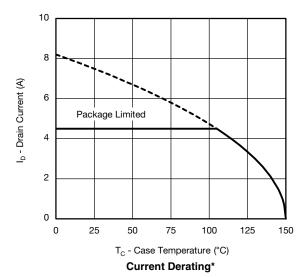
Power Dissipation (W)

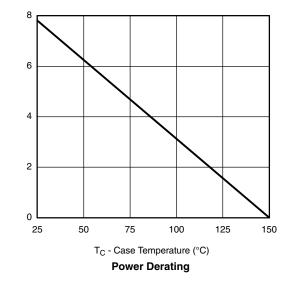
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





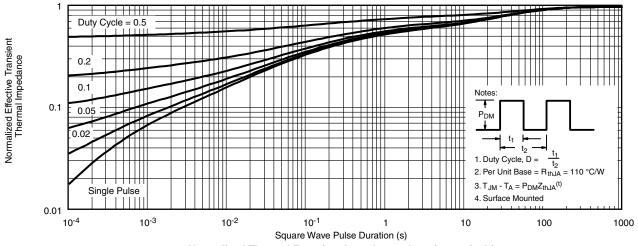
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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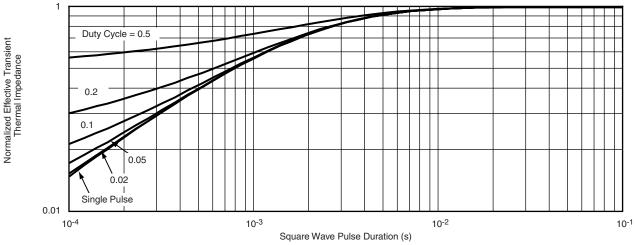
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

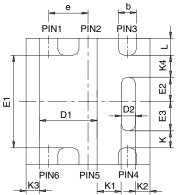
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67314.

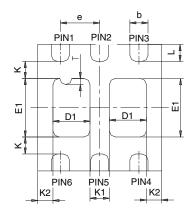




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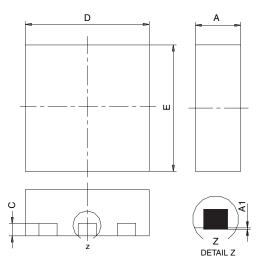
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	M	ILLIMETER	RS		INCHES		MILLIMETERS		INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP		
K1		0.400 TYP			0.016 TYP		0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP					•	•		
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

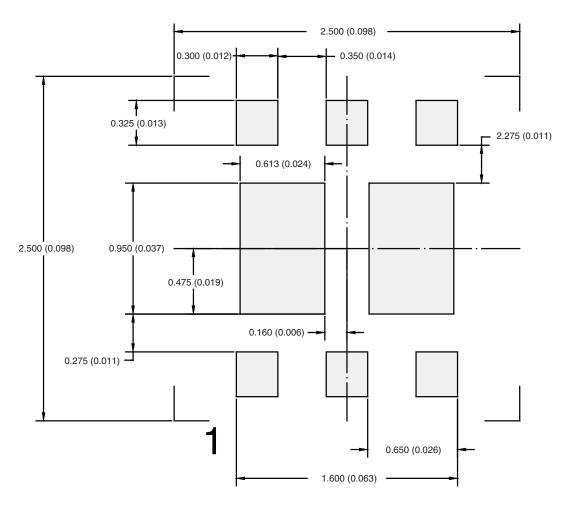
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm/(Inches)

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